

Single 8-Ch/Differential 4-Ch CMOS Analog Multiplexers**Features**

- Low On-Resistance: 240 Ω
- TTL and CMOS Logic Compatible
- Low Power: 30 mW
- Break-Before-Make Switching
- 44-V Power Supply Rating
- Transition Time: 600 ns

Benefits

- Easily Interfaced
- Low Power Consumption
- Low System Crosstalk
- Wide Analog Signal Range

Applications

- Communication Systems
- ATE
- Data Acquisition Systems
- Audio Signal Routing and Multiplexing
- Medical Instrumentation

Description

The DG508A, an 8-channel single-ended analog multiplexer, is designed to connect one of eight inputs to a common output as determined by a 3-bit binary address (A_0, A_1, A_2).

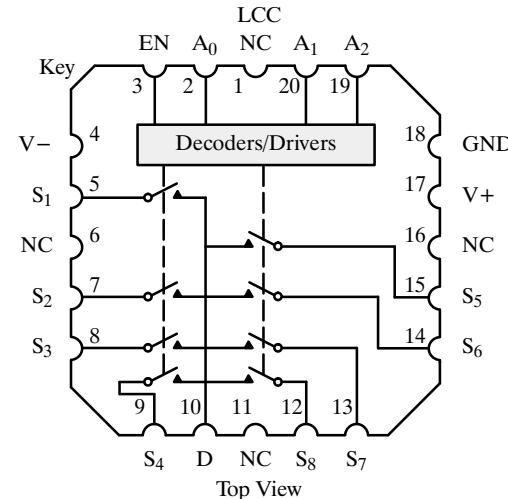
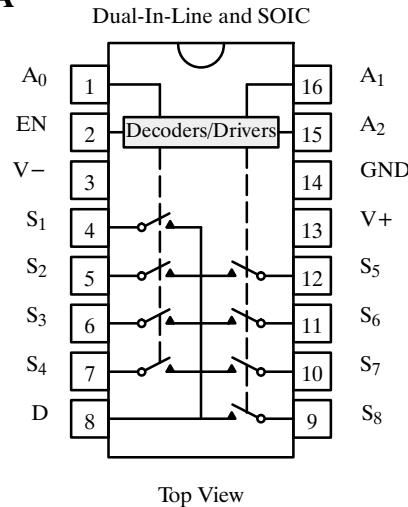
The DG509A, a dual 4-channel analog multiplexer, is designed to connect one of four differential inputs to a common output as determined by its 2-bit binary address (A_0, A_1) logic. Break-before-make switching action protects against momentary shorting of the input signals.

A channel in the on state conducts current equally well in both directions. In the off state each channel blocks voltages up to the power supply rails, normally 30 V peak-to-peak. An enable (EN) function allows for device selection when several multiplexers are used. All control

inputs, address (A_x) and enable (EN) are TTL or CMOS compatible over the full specified operating temperature range.

Fabricated in the Siliconix Plus-40 process, the absolute maximum voltage rating is extended to 44 V, allowing increased operating headroom for standard ± 15 -V signal swings and operation with ± 20 -V supplies. An epitaxial layer prevents latch up.

For applications requiring address data latching, the DG528/529 is recommended. DG408/409 is recommended for higher precision applications. For wideband/video routing and multiplexing, the DG538A is recommended.

Functional Block Diagrams and Pin Configurations**DG508A**

DG508A/509A

TEMIC

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Functional Block Diagrams and Pin Configurations (Cont'd)

Ordering Information — DG508A

Temp Range	Package	Part Number
0 to 70°C	16-Pin Plastic DIP	DG508ACJ
-25 to 85°C	16-Pin CerDIP	DG508ABK
-40 to 85°C	16-Pin Narrow SOIC	DG508ADY
	16-Pin CerDIP	DG508AAK
		DG508AAK/883
	LCC-20	DG508AAZ/883
	16-Pin Sidebrazee	7705201EA
		7705201EC
	16-Pin Flat Pack	7705201FA
		7705201FC
	16-Pin Sidebrazee	JM38510/19007BEA
		JM38510/19007BEC

Truth Table — DG508A

A ₂	A ₁	A ₀	EN	On Switch
X	X	X	0	None
0	0	0	1	1
0	0	1	1	2
0	1	0	1	3
0	1	1	1	4
1	0	0	1	5
1	0	1	1	6
1	1	0	1	7
1	1	1	1	8

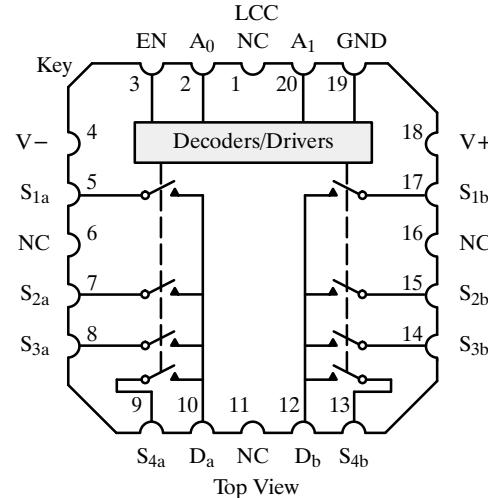
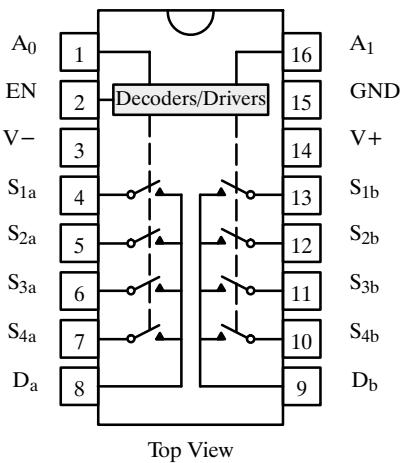
Logic "0" = $V_{AL} \leq 0.8 \text{ V}$

Logic "1" = $V_{AH} \geq 2.4 \text{ V}$

X = Don't Care

DG509A

Dual-In-Line and SOIC



Ordering Information — DG509A

Temp Range	Package	Part Number
0 to 70°C	16-Pin Plastic DIP	DG509ACJ
-25 to 85°C	16-Pin CerDIP	DG509ABK
-40 to 85°C	16-Pin Narrow SOIC	DG509ADY
	16-Pin CerDIP	DG509AAK
		DG509AAK/883
	LCC-20	DG509AAZ/883
	16-Pin Sidebrazee	JM38510/19008BEA
		JM38510/19008BEC

Truth Table — DG509A

A ₁	A ₀	EN	On Switch
X	X	0	None
0	0	1	1
0	1	1	2
1	0	1	3
1	1	1	4

Logic "0" = $V_{AL} \leq 0.8 \text{ V}$

Logic "1" = $V_{AH} \geq 2.4 \text{ V}$

X = Don't Care

Absolute Maximum Ratings

Voltage Referenced to V-

V+	44 V
GND	25 V
Digital Inputs ^a , V _S , V _D	(V-) -2 V to (V+) +2 V or 20 mA, whichever occurs first
Current (Any Terminal, Except S or D)	30 mA
Continuous Current, S or D	20 mA
Peak Current, S or D (Pulsed at 1 ms, 10% Duty Cycle Max)	40 mA
Storage Temperature (K Suffix)	-65 to 150°C
	(J and Y Suffix)	-65 to 125°C

Power Dissipation (Package)^b

16-Pin Plastic DIP ^c	470 mW
16-Pin Narrow SOIC ^c	600 mW
16-Pin CerDIP ^d	900 mW
LCC-20 ^d	900 mW

Notes:

- a. Signals on S_X, D_X or IN_X exceeding V+ or V- will be clamped by internal diodes. Limit forward diode current to maximum current ratings.
- b. All leads soldered or welded to PC board.
- c. Derate 6.3 mW/°C above 75°C.
- d. Derate 12 mW/°C above 75°C.

Specifications^a

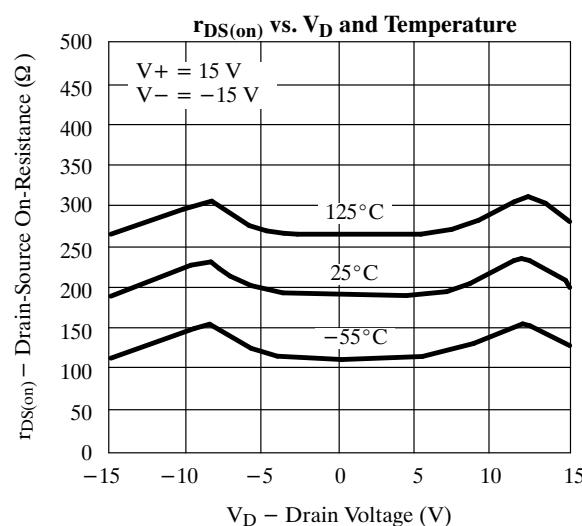
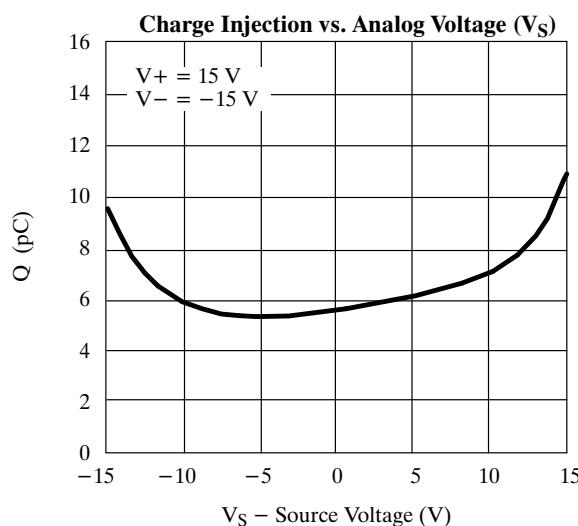
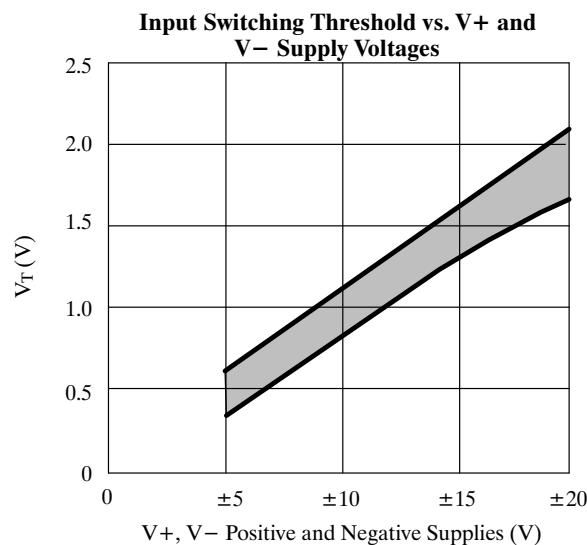
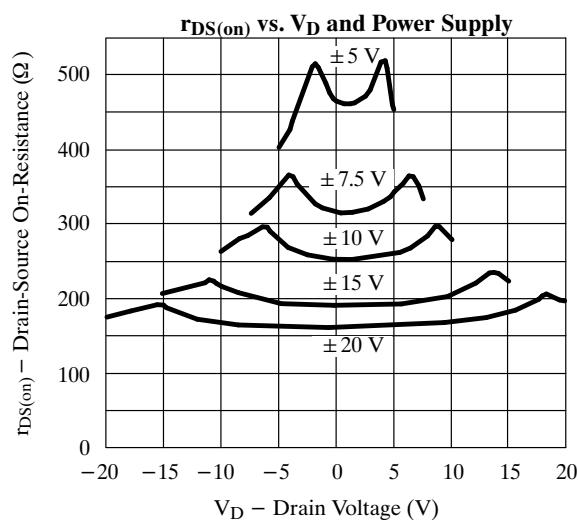
Parameter	Symbol	Test Conditions Unless Otherwise Specified V ₊ = 15 V, V ₋ = -15 V V _{IN} = 2.4 V, 0.8 V ^f	Temp ^b	Typ ^c	A Suffix -55 to 125°C		D Suffix -40 to 85°C		Unit
					Min ^d	Max ^d	Min ^d	Max ^d	
Analog Switch									
Analog Signal Range ^e	V _{ANALOG}		Full		-15	15	-15	15	V
Drain-Source On-Resistance	r _{DS(on)}	V _D = ±10 V, I _S = -200 μA	Room Full	240		400 500		450 550	Ω
r _{DS(on)} Match	Δr _{DS(on)}	-10 V < V _S < 10 V	Room	6					%
Source Off Leakage Current	I _{S(off)}	V _{EN} = 0 V, V _S = ±10 V V _D = ±10 V	Room Full		-1 -50	1 50	-5 -50	5 50	
Drain Off Leakage Current	I _{D(off)}	V _{EN} = 0 V V _D = ±10 V V _S = ±10 V	Room Full	DG508A	-10 -200	10 200	-20 -200	20 200	nA
			Room Full	DG509A	-10 -100	10 100	-20 -100	20 100	
Drain On Leakage Current	I _{D(on)}	V _S = V _D = ±10 V	Room Full	DG508A	-10 -200	10 200	-20 -200	20 200	
			Room Full	DG509A	-10 -100	10 100	-20 -100	20 100	
Digital Control									
Logic Input Current Input Voltage High	I _{AH}	V _A = 2.4 V	Room Full	-0.00 2	-10 -30		-10 -30		μA
		V _A = 15 V	Room Full	0.006		10 30		10 30	
Logic Input Current Input Voltage Low	I _{AL}	V _{EN} = 0 V, 2.4 V, V _A = 0 V	Room Full	-0.00 2	-10 -30		-10 -30		
Dynamic Characteristics									
Transition Time	t _{TRANS}	See Figure 2	Room	0.6		1			μs
Break-Before-Make Time	t _{OPEN}	See Figure 4	Room	0.2					
Enable Turn-On Time	t _{ON(EN)}	See Figure 3	Room	1		1.5			
Enable Turn-Off Time	t _{OFF(EN)}		Room	0.4		1.0			
Charge Injection	Q	See Figure 5	Room	6					pC
Off Isolation	OIRR	V _{EN} = 0 V, R _L = 1 kΩ, C _L = 15 pF V _S = 7 V _{RMS} , f = 500 kHz	Room	68					dB
Logic Input Capacitance	C _{in}	f = 1 MHz	Room	8					pF
Source Off Capacitance	C _{S(off)}	V _{EN} = 0 V, V _S = 0 V, f = 140 kHz	Room	6					pF

Specifications^a

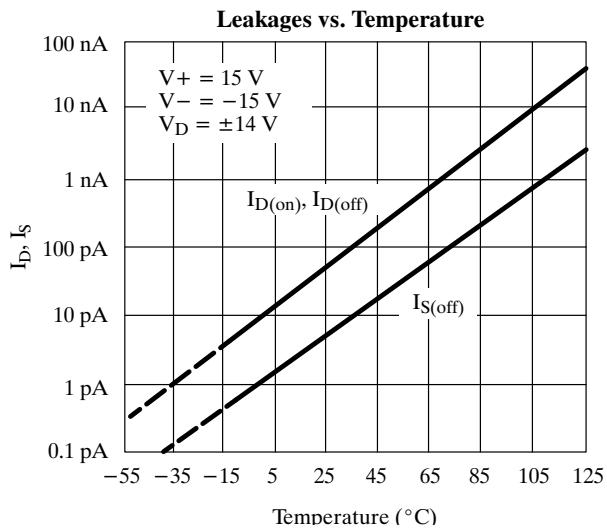
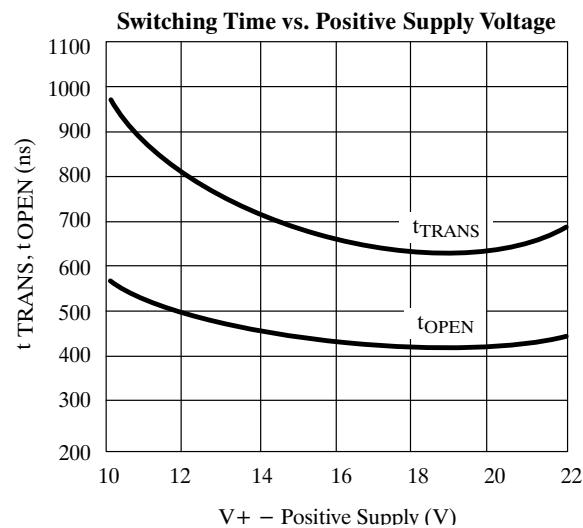
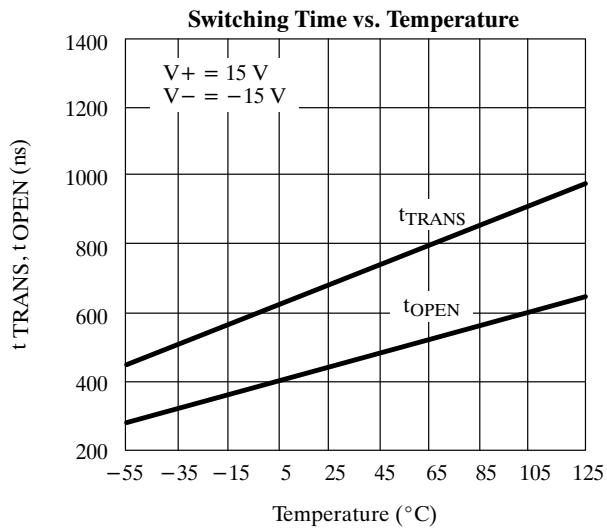
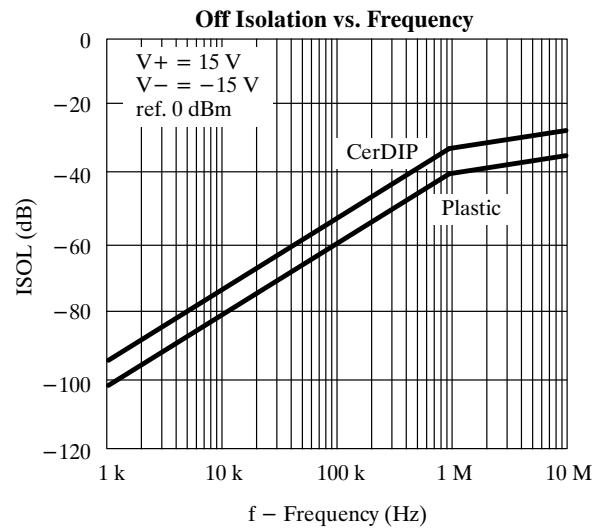
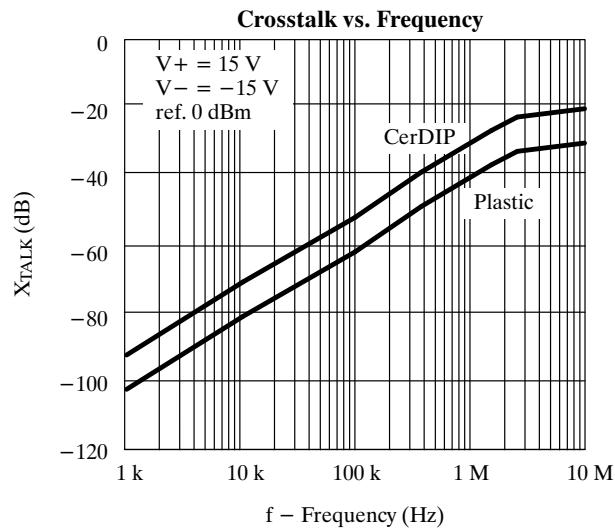
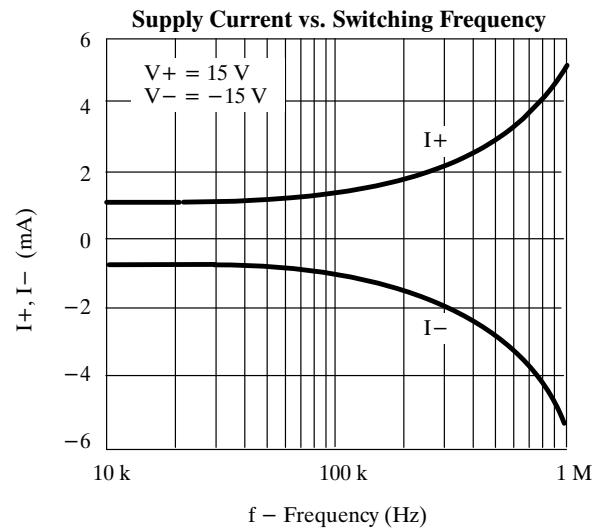
Parameter	Symbol	Test Conditions Unless Otherwise Specified $V_+ = 15 \text{ V}$, $V_- = -15 \text{ V}$ $V_{IN} = 2.4 \text{ V}, 0.8 \text{ V}^f$	Temp ^b	Typ ^c	A Suffix -55 to 125°C		D Suffix -40 to 85°C		Unit
					Min ^d	Max ^d	Min ^d	Max ^d	
Dynamic Characteristics (Cont'd)									
Drain Off Capacitance	C _{D(off)}	$V_{EN} = 0 \text{ V}$, $V_D = 0 \text{ V}$ $f = 140 \text{ kHz}$	DG508A	Room	25				pF
			DG509A	Room	12				
Power Supplies									
Positive Supply Current	I ₊	$V_{EN} = 0 \text{ V}$ or 2.4 V	Room	1.3		2.4		2.4	mA
Negative Supply Current	I ₋		Room	-0.7	-1.5		-1.5		

Notes:

- a. Refer to PROCESS OPTION FLOWCHART (Section 5 of the 1994 Data Book or FaxBack number 7103).
- b. Room = 25°C, Full = as determined by the operating temperature suffix.
- c. Typical values are for DESIGN AID ONLY, not guaranteed nor subject to production testing.
- d. The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this data sheet.
- e. Guaranteed by design, not subject to production test.
- f. V_{IN} = input voltage to perform proper function.

Typical Characteristics

Typical Characteristics (Cont'd)

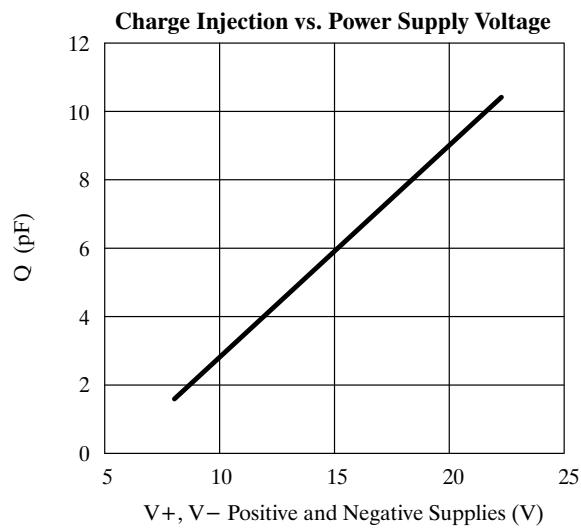
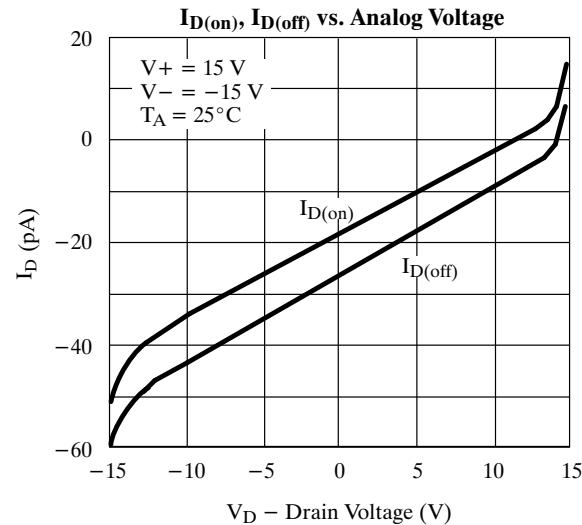
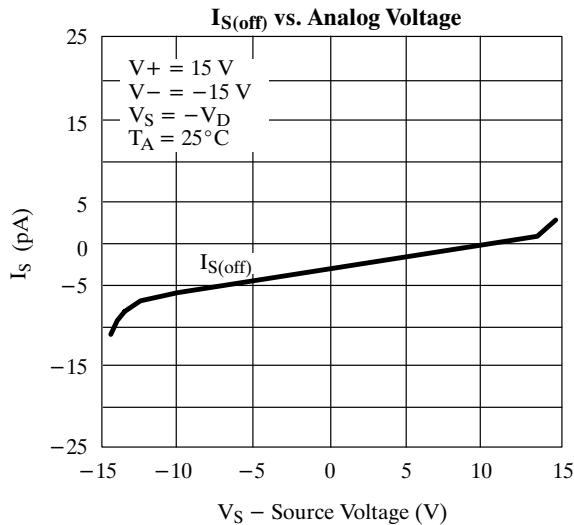


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Typical Characteristics (Cont'd)



Schematic Diagram (Typical Channel)

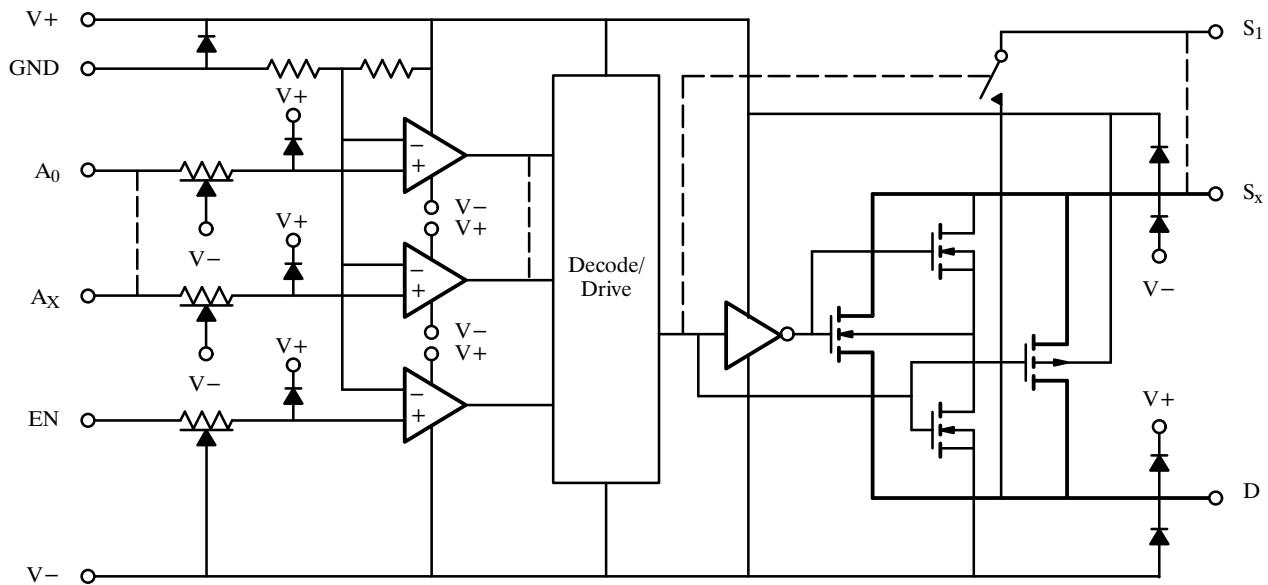


Figure 1.

Test Circuits

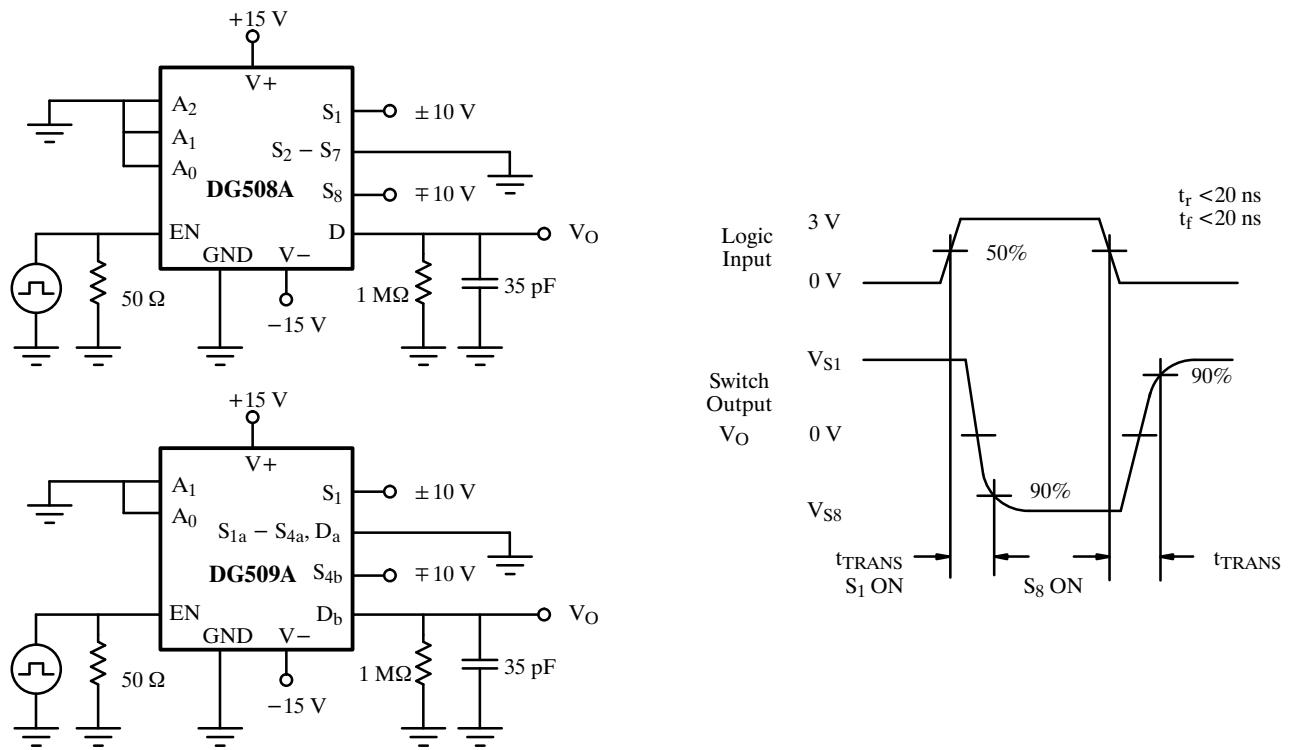


Figure 2. Transition Time

DG508A/509A

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Test Circuits (Cont'd)

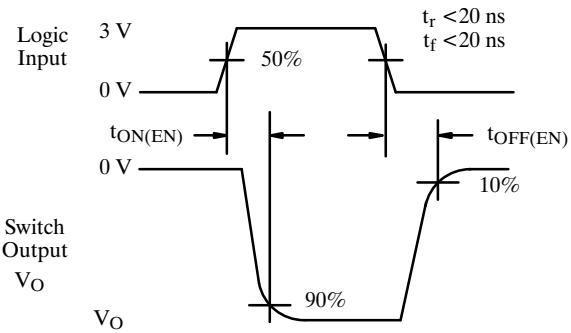
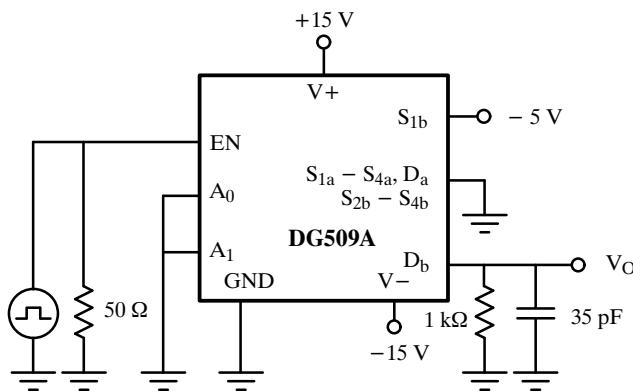
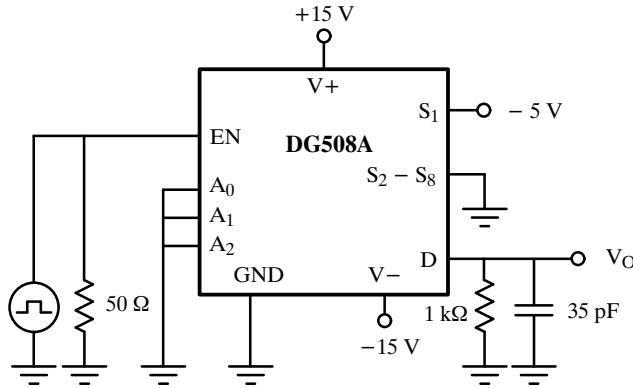


Figure 3. Enable Switching Time

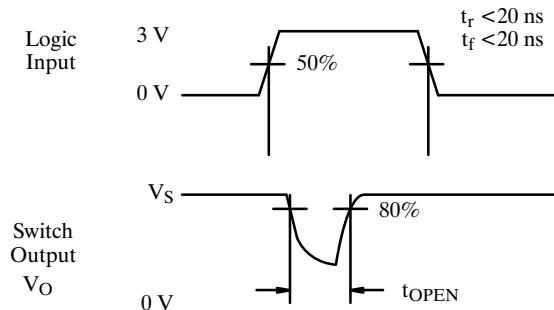
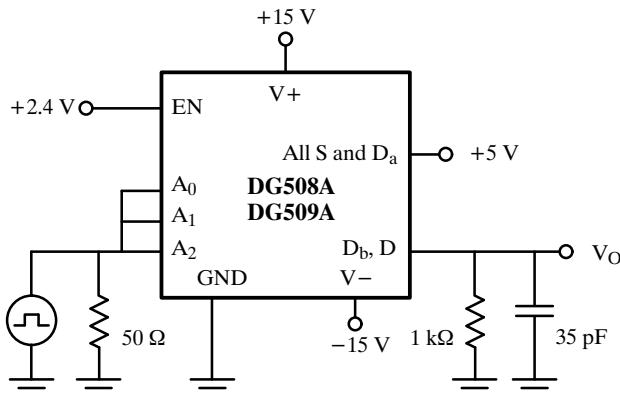
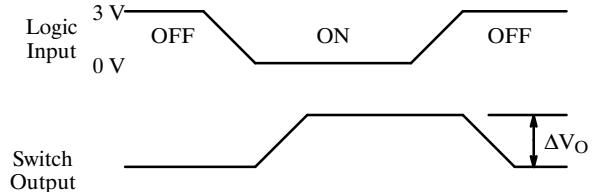
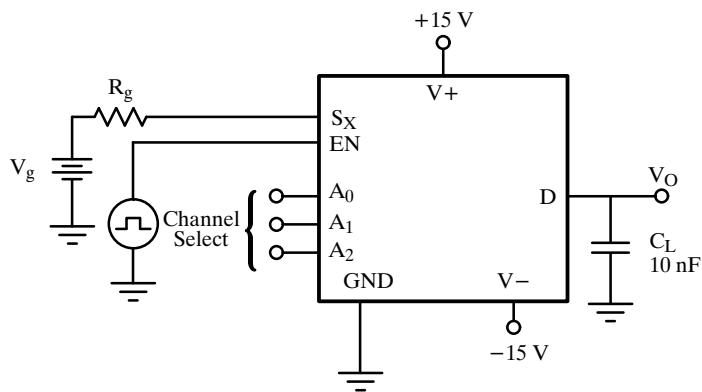


Figure 4. Break-Before-Make Interval

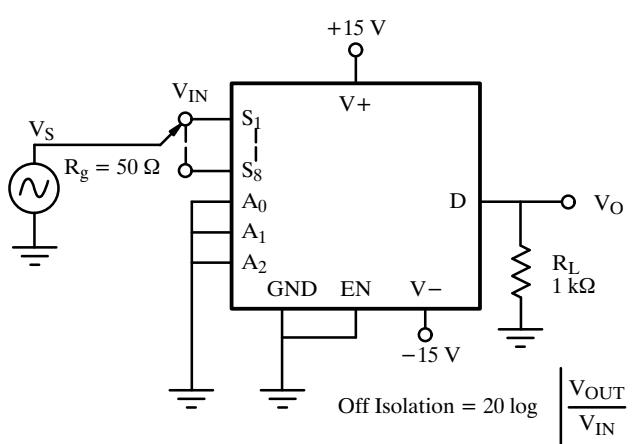
Test Circuits (Cont'd)



ΔV_O is the measured voltage due to charge transfer error Q , when the channel turns off.

$$Q = C_L \times \Delta V_O$$

Figure 5. Charge Injection



$$\text{Off Isolation} = 20 \log \left| \frac{V_{OUT}}{V_{IN}} \right|$$

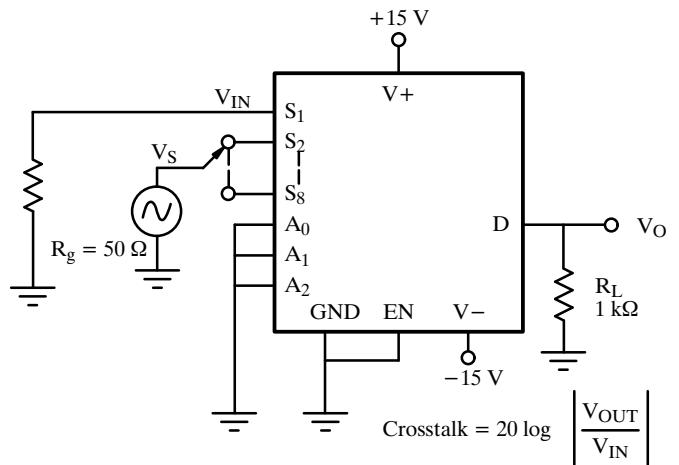
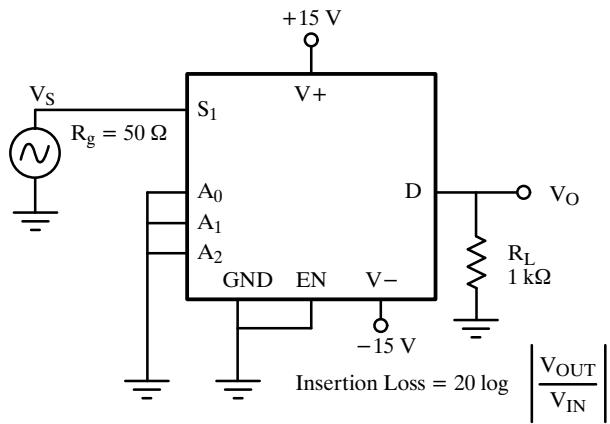


Figure 6. Off Isolation

Figure 7. Crosstalk



$$\text{Insertion Loss} = 20 \log \left| \frac{V_{OUT}}{V_{IN}} \right|$$

Figure 8. Insertion Loss

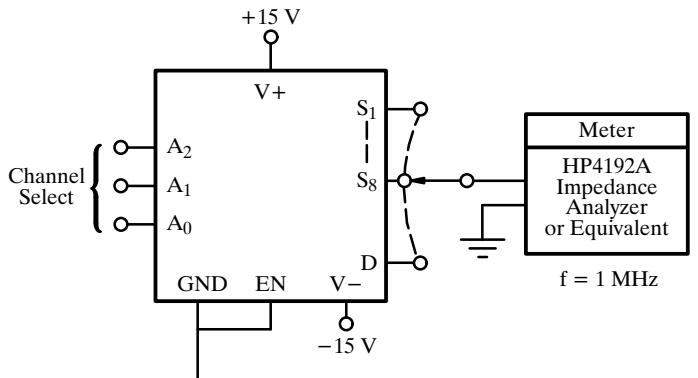


Figure 9. Source Drain Capacitance

Applications

V+ Positive Supply Voltage (V)	V- Negative Supply Voltage (V)	V _{IN} Logic Input Voltage V _{INH(min)/V_{INL(max)}} (V)	V _S or V _D Analog Voltage Range (V)
15	-15	2.4/0.8	-15 to 15
10	-12	2.4/0.8	-12 to 12
12	-10	2.4/0.6	-10 to 10
8 ^b	-8	2.4/0.4	-8 to 8

Notes:

- a. Application Hints are for DESIGN AID ONLY, not guaranteed and not subject to production testing.
- b. Operation below ± 8 V is not recommended.

Overvoltage Protection

A very convenient form of overvoltage protection consists of adding two small signal diodes (1N4148, 1N914 type) in series with the supply pins (see Figure 11). This arrangement effectively blocks the flow of reverse currents. It also floats the supply pin above or below the normal V+ or V- value. In this case the overvoltage signal actually becomes the power supply of the IC. From the point of view of the chip, nothing has changed, as long as the difference between V_S and the V- rail doesn't exceed +44 V. The addition of these diodes will reduce the analog signal range to 1 V below V+ and 1 V above V-, but it preserves the low channel resistance and low leakage characteristics.

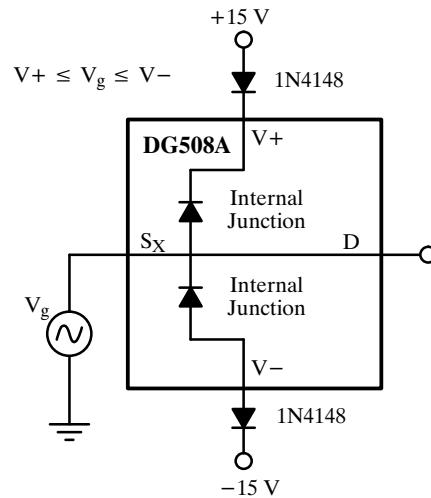


Figure 10. Overvoltage Protection Using Blocking Diodes

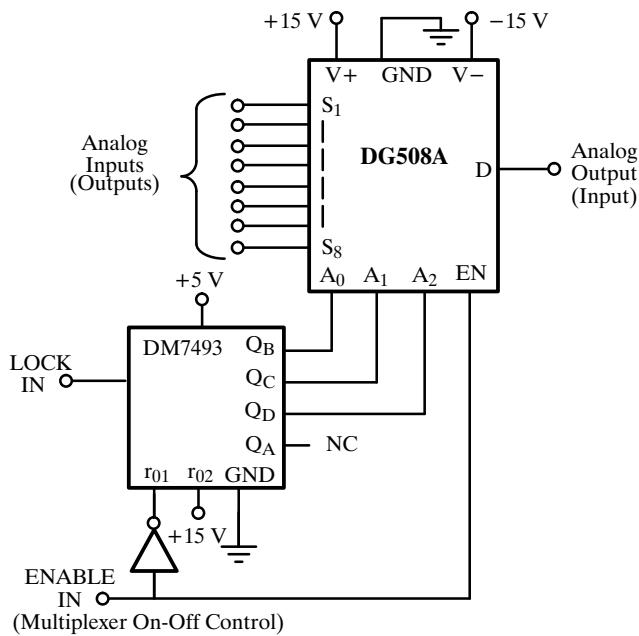


Figure 11. 8-Channel Sequential Multiplexer/
Demultiplexer

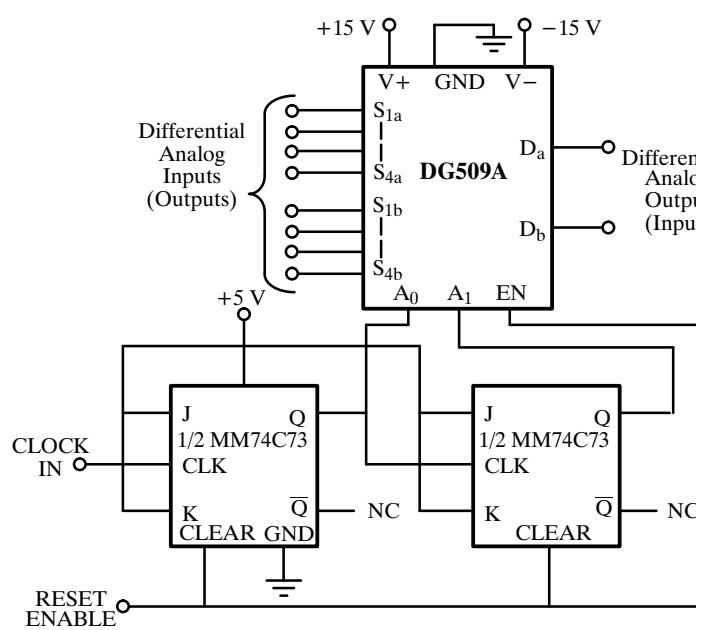


Figure 12. Differential 4-Channel Sequential Multiplex
Demultiplexer